

Isotope effects in multiband superconductors

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Abstract

Isotope effects in a multiband superconductor with a leading interband pairing channel are investigated. A relatively small electron-phonon contribution into the pair-transfer interaction can cause effects of observed magnitude. A multiband model which interpolates the cuprate properties is used for illustrative calculations. Isotope exponents of the transition temperature (T_c), supercarrier density (n_s), paired carrier effective mass (m^*) and of the penetration depth (λ) on the doping scale have been obtained. The known opposite trend of T_c and n_s is reflected. The trends of m^* and λ are similar. In contrast with the usual assumption in the interband case T_c is driven by n_s , which overwhelms m^* .

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1 Introduction

The isotope effect on the superconductivity transition temperature has indicated the participation of the lattice vibrations in the pairing mechanism. In simple metals the superconductivity appears as a pure phonon-mediated

intraband effect due by attractive Fermi-level attached effective electron coupling. For complex materials the deviations from the canonical BCS value $\alpha = 0.5$ become especially exposed.

For cuprate high-temperature superconductors the isotope effect at $O^{16} \rightarrow O^{18}$ substitution has been proven in a number of investigations, e.g. [1-7]. An overall trend of the isotope effect exponent to enhance with lowering transition temperature and vice versa appeared to be characteristic for cuprates. This behaviour of α on the doping phase diagram has stimulated the search for nonphononic pairing mechanisms. It seems that phonon mechanisms cannot compete with electronic (charge or spin) pairing channels for cuprates. However the superconductivity mechanism of cuprates remains still elusive. In the last time multiband approaches with interband interactions seem to become popular [8,9].

Sometimes one asks simply whether the electron-phonon interaction plays an essential role in cuprate superconductors or not [6]. Cuprates are known to be systems with strong electronic correlations and lattice structural effects. Doping induces here phase separation and formation of a defect-polaronic subsystem bearing the doped holes [10,11]. Indications of the influence of phonons on various properties correlated with the superconductivity are known [12,13]. So, the mentioned question must be about the relative contribution of the electron-phonon interaction (intra- and interband) into the cuprate pairing mechanism.

The development of isotope effect investigations concentrates on the CuO_2 -plane magnetic penetration depth λ_{ab}^{-2} represents the superfluid stiffness. It includes the supercarrier number density N_s and the in-plane paired carrier effective mass in the ratio $N_s m_{ab}^{-1}$. In the conventional theory N_s is usually interpreted as the total carrier density. Correspondingly one interpretes the λ_{ab}^{-2} as representing the paired carrier effective mass isotope effect [6-7], because the number of the normal state carriers does not change by isotopic substitution [3]. Such neglecting of the isotope effect contribution from N_s into λ_{ab}^{-2} cannot be justified in general. In nonconventional pairing mechanisms only a part of normal state carriers will be paired even at $T = 0$. The isotope change of N_s cannot be ignored and can contribute to the understanding of the pairing mechanism.

This is the case in multiband superconductivity with interband pairing interaction. And more. A moderate electron-phonon contribution in the (interband) pairing interaction as compared with a nonphononic one does

not mean necessarily a small outcome in the isotope effect. In the framework of the two-band superconductivity [14,15] with the interband pair-transfer channel [16] it has been shown that a small ($< 10\%$) contribution of the interband electron-phonon coupling into the whole interband coupling can cause a remarkable isotope effect [16-18]. The magnitude of α has been found to vary with T_c just in the same opposite manner as observed in cuprates. The promising outcome of two-band models for the explanation of isotope effect peculiarities has not been found much attention, however see [9,18-21].

The authors of the present contribution have developed a simple descriptive (multiband) model of cuprate superconductivity [22,23]. It is based on an electron spectrum created and evolving with doping. The interband pair transfer channel operates between the itinerant and defect subsystem states. This model explains qualitatively the behaviour of cuprate energetic [23,24] and thermodynamic [25,26] characteristics on the whole doping scale. In the present communication the isotope effect exponents are calculated using this model. The characteristic behaviour of α with T_c is obtained. The supercarrier density isotope exponent follows the trend of α . The paired carrier effective mass isotope exponent is negative at underdoping. Contrary to usual assumptions the superfluid density isotope effect is determined by the supercarrier density change in collaboration with the effective mass contribution.

2 The isotope effect characteristics and the vibronic constant

The isotope effect characteristic exponents are defined as

$$\alpha_i = \frac{d \ln X}{d \ln M} C_i; \quad (1)$$

where X designates the physical quantity under consideration and i specifies the atomic mass (M_i) undertaken to be isotopically substituted. The effective mass (M) attributed to the active vibration mode can be a complicated function of the masses of the atoms in the unit cell. This is accounted by $C_i = d \ln M / (d \ln M_i)^{-1}$. The oxygen isotope effect in cuprates can be considered as caused by the dominating $O^{16} \rightarrow O^{18}$ mass change. In (1) for T_c corresponds α_n { to supercarrier density n_s ; α_m { to supercarrier effective

mass m_{ab} , $\{\}$ to the penetration depth λ_{ab} and $\{\}$ to the superfluid stiffness κ_{ab}^2 .

The penetration depth is expressed as

$$\lambda_{ab}^2 = \frac{m_{ab} c^2}{4 e^2 N_s} \quad (2)$$

with $N_s = n_s p N_0$, where $p N_0$ stands for the normal state carrier concentration at hole doping p . One sees that

$$\frac{m}{m_{ab}} = \frac{T_c}{m_{ab}} \frac{dm_{ab}}{dT_c}; \quad (3)$$

$$\begin{aligned} &= \frac{1}{2} (m_{\text{m}} - m_{\text{n}}) \\ &= \frac{1}{2} : \end{aligned} \quad (4)$$

The interelectronic effective coupling mediated by phonons of frequency ω is characterized by

$$V_{\omega}(\mathbf{k}; \mathbf{k}^0) = \frac{g_{\omega}(\mathbf{k} - \mathbf{k}^0) g_{\omega}(\mathbf{k} + \mathbf{k}^0)}{[\epsilon(\mathbf{k}) - \epsilon(\mathbf{k}^0)]^2} : \quad (5)$$

Here g_{ω} are the coefficients of the linear electron-phonon coupling.

Note that in the intraband case $\omega = \omega_0$, as also in the interband case $\omega = \omega_0$, the attractive part of the coupling does not depend on M because $g_{\omega} = \hbar \omega_0 / 2M$ and $\omega_0 \propto M^{-1/2}$ (in the BCS theory M enters only through the integration borders). In a large part of the \mathbf{k} space, especially in the interband case, where $\hbar \omega(\mathbf{k} - \mathbf{k}^0)$ can be neglected in comparison with $\hbar \omega(\mathbf{k}) + \hbar \omega(\mathbf{k}^0)$, so that $V > 0$ corresponds to repulsion, one has $V \propto M^{-1}$. In the case of interband coupling the result $V_{\omega_0} \propto M^{-1}$ is of special significance because the repulsive interelectron coupling can then lead to pairing [27] and V can exert immediate influence on superconductivity associated properties.

In the case of dominating interband pairing interaction the Expr.(1), leaving out C_1 , can be presented as

$$\chi = Z \frac{W}{X} \frac{dX}{dW}; \quad (6)$$

where

$$Z = \frac{V}{W} \quad (7)$$

determines the relative electron-phonon contribution to the whole interband pairing interaction $W = V + U$ (U is the Coulomb contribution).

3 The model and the calculation scheme

The physical model used [23] which interpolates the known cuprate properties can be shortly described as follows. The CuO_2 plane electronic background includes a defect subsystem bearing the doped holes besides the itinerant hole poor material. Doping creates new defect states near the top of the valence band (ϵ) in the charge-transfer gap. These states are described by two subband components (ϵ_{\pm}) representing the "hot" ($\epsilon_{\pm 0}$)-type and "cold" ($\epsilon_{\pm 2}$)-type regions of the momentum space. Bare normal state gaps between these subbands and the valence band are supposed to be closed by progressive doping (subband bottoms evolve down). The doping concentrations at which the band overlaps are reached correspond to special (critical) points on the phase diagram.

There are four regions of the doping in the model with specific dispositions of the band components and the chemical potential: a) at very underdoping the "young" defect subsystem is gapped; b) in the underdoped region the ϵ_{\pm} bands overlap and ϵ is shifted down to intersect both of them; c) the effectively doped region is headed by the optimal overlapping of ϵ_{\pm} bands, all being intersected by the chemical potential; d) at extended overdoping ϵ intersects only the overlapping ϵ_{\pm} bands. The difference between the itinerant and defect carriers becomes progressively washed up with doping. The ϵ_{\pm} and ϵ band densities of states are constant, for the valence band it reduces with doping.

A plausible parameter set [23] is used for illustrative calculations. The doped hole concentrations are scaled to $T_c(\text{max})$ being reached at $p = 0.16$.

The effective Hamiltonian with the interband pairing channel between the defect and itinerant states reads

$$H = \sum_{\mathbf{k},s} \epsilon(\mathbf{k}) a_{\mathbf{k},s}^{\dagger} a_{\mathbf{k},s} + W \sum_{\mathbf{k},s} \sum_{\mathbf{k}',s'} \sum_{\mathbf{q}} a_{\mathbf{k},s}^{\dagger} a_{\mathbf{k}+\mathbf{q},s'}^{\dagger} a_{\mathbf{k}',s} a_{\mathbf{k}'-\mathbf{q},s'} : \quad (8)$$

Here $\epsilon_s = \epsilon_{\mathbf{k},s}$, s is the spin index, N counts the bands and \mathbf{q} is the pair momentum with the components from the same bands. The superconductivity gap system corresponding to (8) is

$$\begin{aligned} &= W \sum_{\mathbf{k};s} \epsilon_{\mathbf{k},s} E_{\mathbf{k}}^{-1} \tanh \frac{E_{\mathbf{k}}}{2} \\ &= W \sum_{\mathbf{k}} \epsilon_{\mathbf{k}} E_{\mathbf{k}}^{-1} \tanh \frac{E_{\mathbf{k}}}{2} \end{aligned} \quad (9)$$

with the usual form of the quasiparticle energies $E_{\mathbf{k}} = \sqrt{\epsilon_{\mathbf{k}}^2 + \Delta_{\mathbf{k}}^2}$ and $\beta = k_B T$.

Here \int means the integration over the different energy intervals corresponding to the defect system subbands $\epsilon = \epsilon_1, \dots, \epsilon_N$. The density of the paired carriers is

$$n_s = \frac{1}{2} \sum_{\mathbf{k}} \frac{\epsilon_{\mathbf{k}}^2}{E_{\mathbf{k}}^2} \tanh^2 \frac{E_{\mathbf{k}}}{2} + \sum_{\mathbf{k}} \frac{\epsilon_{\mathbf{k}}^2}{E_{\mathbf{k}}^2} \tanh^2 \frac{E_{\mathbf{k}}}{2} : \quad (10)$$

The free energy corresponding to the (1) has been calculated analogously to [18]. Our two-component system possesses two order parameters [18] of different criticality. The "soft" one of the Goldstone in phase type is connected to amplitudes of the two superfluids. It determines both the superconducting gaps and behaves critically at T_c with the corresponding critical coherence length characterizing the fluctuations. The paired carrier effective mass associated with this mode reads

$$m_{ab} = \frac{1}{2} \frac{(\epsilon_1 + \epsilon_2)(\epsilon_1 + \epsilon_2)}{(\epsilon_1 + \epsilon_2) m_1 + (\epsilon_1 + \epsilon_2) m_1} ; \quad (11)$$

Here the band effective masses are determined by the corresponding densities of states. For ϵ_1 being not too close to limiting energies ϵ_0 and ϵ_c of the bands one has

$$= W \ln \frac{2}{\epsilon_c^2} j_0 j_c j ; \quad (12)$$

$$= \frac{7}{2} (3) W j_0 j (\epsilon_c)^2 ; \quad (13)$$

when ϵ is located in the integration region ($\zeta(x)$ is the zeta-function; $\gamma = \exp(0.577)$).

If ϵ lies out of the band $\epsilon = 0$ and

$$\gamma = W \ln \frac{c}{0} : \quad (14)$$

4 Isotope effects dependences on doping

The transition temperature and supercarrier density isotope effect exponents have been calculated numerically using Expr.(9) and (10). W has been varied according to (6) and the necessary derivatives have been determined from the doping dependence curves.

The calculated $\gamma(p)$ curve corresponding to $Z = 0.05$ is shown in Fig.1. The decrease of γ with increasing T_c is illustrated. The major result consists in that even a contribution of some percent from the electron-phonon interaction to the interband pairing channel can lead to "normal valued" transition temperature isotope exponents. This can be understood from the approximate formulae for T_c of the present approach [16]. Here an electron scale energy is cut off by an exponential factor containing $V \propto M^{-1}$. Then γ is found to be large for stronger cut-off.

The experimental doping dependence of γ in cuprates has been approximated in [28] by the expression $\gamma = 0.25 T_c T_{cm}^{-1} (1 - T_c T_{cm}^{-1})$ (T_{cm} is the maximum T_c) for the underdoped region. Our result is compared with this curve in Fig.2 and is exposed as being too slow. One source for this discrepancy can be the dependence of Z on doping. The enhancement of the electron-phonon relative contribution into W with progressive underdoping can improve the result.

The isotope effect behaviour for the supercarrier density n_s is of the same nature as $\gamma(p)$ because the T_c bell-like dependence is driven by the supercarrier density. It changes according to the efficiency of the interband pairing with varying ϵ and bands disposition. The supercarrier fraction n_{sp} behaviour explains in a natural way the T_c quenching at overdoping on the background of enhanced doped hole concentration p [29].

The paired carrier effective mass isotope effect exponent dependence on doping is shown in Fig.3. The negative values of γ_m at underdoping agree

with the observed trend found from superfluid stiffness data supposing the absence of the contribution from the paired carrier density [6,7]. Theoretical absolute values of κ_m are small as compared with κ_n which is in the same order as κ_n . As the result the overall negative isotope exponent of the plane ($T = 0$) penetration depth is determined by both κ_n and κ_m , see (4). The

(p) theoretical curve is given in Fig.4. Its behaviour and observed order of magnitude are determined by the isotope effect in the paired carrier density overwhelming the paired carrier effective mass contribution. This is in contrast with the widely accepted assumption that the penetration depth is determined by the whole amount of carriers present, which does not change at isotope substitution [13,28], however, cf. [30]. The presence of paired carrier density isotope effect is characteristic for multiband superconductivity with interband pairing. There is an essential difference with the conventional one-band case where all the (normal state) carriers in the active momentum region will be paired at $T = 0$.

Experimentally the superfluid density oxygen isotope effect exponent is estimated to be around 0.5. A representative value of κ_m from Fig.4 leaves one for $\kappa_n = 2$ in this scale.

The present work shows that the electron-phonon interaction can cause in multiband superconductors essential lattice-connected effects without playing a leading role in the pairing mechanism. The paired carrier density isotope effect must be taken into account at this.

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References

1. J.P. Franck in: Physical Properties of High-Temperature Superconductors, ed. D.M. Ginsburg, World Sci., 1994, 4, p. 189.
2. D. Zech et al., Nature 371, 681 (1994).
3. G. Zhao et al., J. Phys. Cond. Mat. 10, 9055 (1998).

4. G Zaho, V K irtikar, D E M orris, Phys. Rev. B 63, 220506(R) (2001).
5. R K hasanov, J. Phys. Cond. M at. 16, S 4439 (2004).
6. R K hasanov et al, Phys. Rev. Lett. 92, 057602 (2004).
7. J.L.Tallon et al, Phys. Rev. Lett. 94, 237002 (2005).
8. A B ianconi, J. Supercond. 18, 625 (2005).
9. A B ianconi, M F ilippi, in: Sym m etry and H eterogeneity in H igh Tem – perature Superconductors, ed. A B ianconi, Springer, 2006, p. 21.
10. Phase Separation in Cuprate Superconductors, eds. K A M üller and G Benedek, W orld Sci, 1993.
11. K A M üller, Physica C 341-348, 11 (2000).
12. S J L B illinge, T E gam i, in: Lattice E ffects in H igh- T_c Superconductors, ed. Y B ar-Yam , W orld Sci, 1992, p. 23.
13. T E gam i et al, Physica B 316-317, 62 (2002).
14. H Suhl, B T M atthias, L R W alker, Phys. Rev. Lett. 3, 552 (1959).
15. V A M oskalenko, Fiz. M et. M etalloved. 8, 503 (1959).
16. N K risto el, P K onsin, T O rd, Riv. Nuovo C in ento 17, 1 (1994).

17. P K onsin, N K risto el, T .O rd, *Annalen der Physik* 2, 279 (1993).
18. T .O rd, N K risto el, *phys. stat. sol. b* 216, 1049 (1999).
19. A S A lexandrov, *Physica C* 363, 231 (2001).
20. A Busm ann-H older et al, *Europhys. Lett.* 72, 423 (2005).
21. T D ahm , *Phys. Rev. B* 61, 6381 (2000).
22. N K risto el, P Rubin, *Solid State Comm un.* 122, 265 (2002).
23. N K risto el, P Rubin, *Physica C* 402, 257 (2004).
24. N K risto el, P Rubin, in: *Symmetry and Heterogeneity in High Tem - perature Superconductors*, ed. A Bianconi, Springer, 2006, p. 55.
25. N K risto el, P Rubin, *Phys. Lett. A* (2006).
26. N K risto el, T .O rd, P Rubin, *Physica C* (2006).
27. J K ondo, *Progr. Theor. Phys.* 29, 1 (1963).
28. T Schneider, H Keller, *Phys. Rev. Lett.* 69, 3374 (1992).
29. N K risto el, P Rubin, *J. Supercond.* 18, 705 (2005).
30. A B ill, V Z K resin, S A W olf, *Phys. Rev. B* 57, 10814 (1998).

Figure Captions

Fig.1. The transition temperature isotope effect exponent vs doping.

Fig.2. The comparison of calculated (full line) with the averaged experimental data in the underdoped region.

Fig.3. The paired carrier effective mass isotope effect exponent on the doping scale.

Fig.4. The penetration depth isotope effect exponent theoretical dependence on doping.







